

# Hyperfast Rectifier, 1 A FRED Pt®

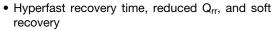
Anode





| PRODUCT SUMMARY                  |                |  |  |  |
|----------------------------------|----------------|--|--|--|
| Package                          | SMA (DO-214AC) |  |  |  |
| I <sub>F(AV)</sub>               | 1 A            |  |  |  |
| $V_{R}$                          | 100 V          |  |  |  |
| V <sub>F</sub> at I <sub>F</sub> | 0.68 V         |  |  |  |
| t <sub>rr</sub>                  | 25 ns          |  |  |  |
| T <sub>J</sub> max.              | 175 °C         |  |  |  |
| Diode variation                  | Single die     |  |  |  |

#### **FEATURES**





RoHS

COMPLIANT HALOGEN

FREE

- 175 °C maximum operating junction temperature
- Specified for output and snubber operation
- Low forward voltage drop
- · Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912">www.vishay.com/doc?99912</a>

#### **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, as high frequency rectifiers, and freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

| ABSOLUTE MAXIMUM RATINGS                    |                                   |   |             |       |  |  |
|---|-----------------------------------|---|-------------|-------|--|--|
| PARAMETER                                   | SYMBOL                            | TEST CONDITIONS                           | VALUES      | UNITS |  |  |
| Peak repetitive reverse voltage             | $V_{RRM}$                         |   | 100         | V     |  |  |
| Average rectified forward current           | I <sub>F(AV)</sub>                | T <sub>Sp</sub> = 158 °C                  | 1           | А     |  |  |
| Non-repetitive peak surge current           | I <sub>FSM</sub>                  | T <sub>J</sub> = 25 °C, 6 ms square pulse | 50          | _ A   |  |  |
| Operating junction and storage temperatures | T <sub>J</sub> , T <sub>Stg</sub> |   | -55 to +175 | °C    |  |  |

| <b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified) |                 |  |      |      |      |       |
|--|-----------------|--|------|------|------|-------|
| PARAMETER  | SYMBOL          | TEST CONDITIONS  | MIN. | TYP. | MAX. | UNITS |
| Breakdown voltage, blocking voltage  | $V_{BR}, V_{R}$ | I <sub>R</sub> = 100 μA                                | 100  | -    | -    |       |
| Forward voltage, per diode V <sub>F</sub>  | V               | I <sub>F</sub> = 1 A                                   | -    | 0.82 | 0.90 | V     |
|  | VF              | I <sub>F</sub> = 1 A, T <sub>J</sub> = 125 °C          | -    | 0.68 | 0.76 |       |
| Reverse leakage current, per diode   | ı               | $V_R = V_R$ rated                                      | -    | -    | 2    |       |
|  | I <sub>R</sub>  | $T_J = 125 ^{\circ}\text{C},  V_R = V_R  \text{rated}$ | -    | 0.6  | 8    | μA    |
| Junction capacitance   | C <sub>T</sub>  | V <sub>R</sub> = 100 V                                 | -    | 8.5  | -    | pF    |



| <b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified) |                  |   |   |   |      |      |       |
|---|------------------|---|---|---|------|------|-------|
| PARAMETER   | SYMBOL           | TEST CO   | TEST CONDITIONS   |   | TYP. | MAX. | UNITS |
|   |                  | $I_F = 1.0 \text{ A}, dI_F/dt = 50 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$ |   | - | 24   | -    |       |
| Reverse recovery time   |                  | $I_F = 0.5 \text{ A}, I_R = 1 \text{ A}, I_{rr} = 0.25 \text{ A}$             |   | - | -    | 25   | ns    |
|   | t <sub>rr</sub>  | T <sub>J</sub> = 25 °C  | $I_F = 1 \text{ A},$ $dI_F/dt = 200 \text{ A/}\mu\text{s},$ $V_R = 160 \text{ V}$ | - | 15.2 | -    | - 115 |
|   |                  | T <sub>J</sub> = 125 °C   |   | - | 21   | -    |       |
| Peak recovery current   | I <sub>RRM</sub> | T <sub>J</sub> = 25 °C  |   | - | 1.38 | -    | A     |
|   |                  | T <sub>J</sub> = 125 °C   |   | - | 2    | -    |       |
| Reverse recovery charge   | Q <sub>rr</sub>  | T <sub>J</sub> = 25 °C  |   | - | 10.6 | -    | nC    |
|   |                  | T <sub>J</sub> = 125 °C   |   | - | 21   | -    | 110   |

| THERMAL - MECHANICAL SPECIFICATIONS            |                                   |   |      |       |                 |       |
|--|-----------------------------------|---|------|-------|-----------------|-------|
| PARAMETER                                      | SYMBOL                            | TEST CONDITIONS                                       | MIN. | TYP.  | MAX.            | UNITS |
| Maximum junction and storage temperature range | T <sub>J</sub> , T <sub>Stg</sub> |   | -55  | 1     | 175             | °C    |
| Thermal resistance, junction to case           | $R_{thJC}$                        | Device mounted on PCB with 2 x 3.5 mm soldering lands | ı    | 11    | 21              | °C/W  |
| Approximate weight                             |                                   |   |      | 0.07  | ='              | g     |
| Approximate weight                             |                                   |   |      | 0.002 |                 | oz.   |
| Marking device                                 |                                   | Case style SMA (DO-214AC)                             |      | 11    | <del>-</del> 11 | •     |

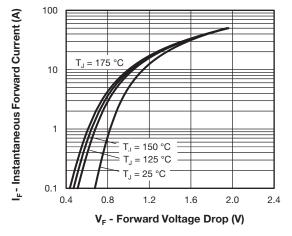


Fig. 1 - Typical Forward Voltage Drop Characteristics

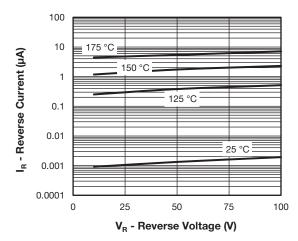


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

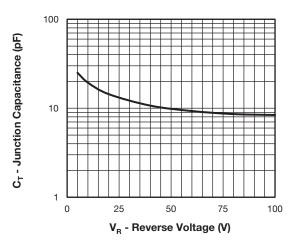


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

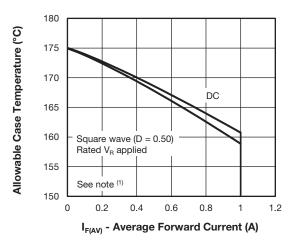


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

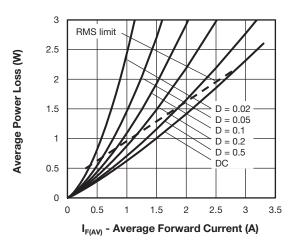


Fig. 5 - Forward Power Loss Characteristics

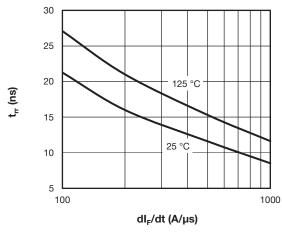


Fig. 6 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

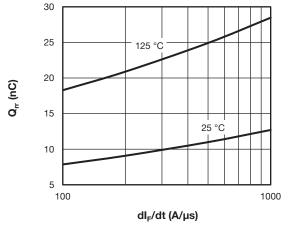
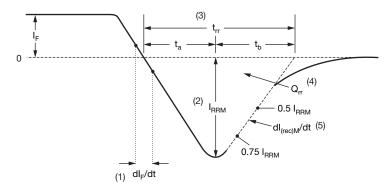


Fig. 7 - Typical Stored Charge vs.  $dI_F/dt$ 

#### Note

<sup>(1)</sup> Formula used: T<sub>C</sub> = T<sub>J</sub> - (Pd + Pd<sub>REV</sub>) x R<sub>th,JC</sub>; Pd = Forward power loss = I<sub>F(AV)</sub> x V<sub>FM</sub> at (I<sub>F(AV)</sub>/D) (see fig. 5); Pd<sub>REV</sub> = Inverse power loss = V<sub>R1</sub> x I<sub>R</sub> (1 - D); I<sub>R</sub> at V<sub>R1</sub> = rated V<sub>R</sub>

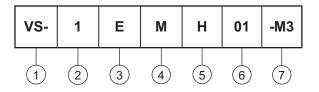


- (1) dl<sub>F</sub>/dt rate of change of current through zero crossing
- (4)  $Q_{rr}$  area under curve defined by  $t_{rr}$  and  $l_{RRM}$
- (2) I<sub>RRM</sub> peak reverse recovery current
- $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$
- (3) t<sub>rr</sub> reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75 I<sub>RBM</sub> and 0.50 I<sub>RBM</sub> extrapolated to zero current.
- (5)  $dI_{(rec)M}/dt$  peak rate of change of current during  $t_b$  portion of  $t_{rr}$

Fig. 8 - Reverse Recovery Waveform and Definitions

### **ORDERING INFORMATION TABLE**

**Device code** 



- 1 Vishay Semiconductors product
- 2 Current rating (1 = 1 A)
- 3 Circuit configuration:

E = single diode

- 4 M = SMA package
- **|5|** Process type,

H = hyperfast recovery

- 6 Voltage code (01 = 100 V)
- 7 -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

| ORDERING INFORMATION (Example)   |      |      |                                   |  |  |  |
|--|------|------|-----------------------------------|--|--|--|
| PREFERRED P/N QUANTITY PER REEL MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION |      |      |                                   |  |  |  |
| VS-1EMH01-M3/5AT   | 7500 | 7500 | 13"diameter plastic tape and reel |  |  |  |

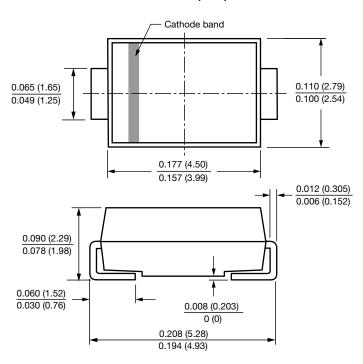
| LINKS TO RELATED DOCUMENTS          |                          |  |  |  |
|-------------------------------------|--------------------------|--|--|--|
| Dimensions www.vishay.com/doc?95400 |                          |  |  |  |
| Part marking information            | www.vishay.com/doc?95472 |  |  |  |
| Packaging information               | www.vishay.com/doc?95404 |  |  |  |



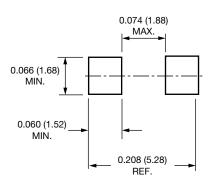
## **SMA**

### **DIMENSIONS** in inches (millimeters)

### **DO-214AC (SMA)**



### Mounting Pad Layout





## **Legal Disclaimer Notice**

Vishay

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